



Addendum

## Addendum: Rivera, I.; Avila, A.; Wang, J. Fourth-Order Contour Mode ZnO-on-SOI Disk Resonators for Mass Sensing Applications. *Actuators* 2015, 4, 60–76

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Academic Editor: Delbert Tesar

Received: 31 August 2016; Accepted: 13 September 2016; Published: 23 September 2016

The authors wish to update the Acknowledgments section in their paper published in *Actuators* [1], doi:10.3390/act4020060, http://www.mdpi.com/2076-0825/4/2/60.

**Acknowledgments:** This work was sponsored in part by a research award from Uninorte-Colombia (COLCIENCIAS Contract #478-2012, Code: 121556933939). The earlier MEMS resonator device development efforts were supported by a grant from the National Science Foundation (ECCS 0925929). All the device microfabrication processes were performed at the Nanotechtology Research and Education Center (NREC) at the University of South Florida, and in particular Robert Tufts and Richard Everly have been helpful in providing training and technical support.

## Reference

1. Rivera, I.; Avila, A.; Wang, J. Fourth-Order Contour Mode ZnO-on-SOI Disk Resonators for Mass Sensing Applications. *Actuators* **2015**, *4*, 60–76. [CrossRef]



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